HGB110N10SL , HGP110N10SL P-1

100V N-Ch Power MOSFET

Feature

◇ High Speed Power Switching, Logic Level
◇ Enhanced Body diode dv/dt capability
◇ Enhanced Avalanche Ruggedness
◇ 100% UIS Tested, 100% Rg Tested
◇ Lead Free, Halogen Free

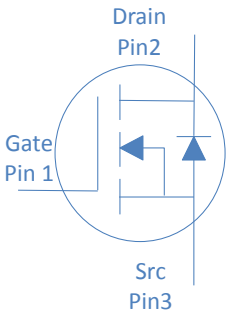
V_{DS}			100	V
$R_{DS(on),typ}$	TO-263	V_{GS}=10V	8.7	mΩ
$R_{DS(on),typ}$		V_{GS}=4.5V	10.7	mΩ
$R_{DS(on),typ}$	TO-220	V_{GS}=10V	9.0	mΩ
$R_{DS(on),typ}$		V_{GS}=4.5V	11	mΩ
$I_{D\ (Sillicon\ Limited)}$			73	A

Application

◇ Synchronous Rectification in SMPS
◇ Hard Switching and High Speed Circuit
◇ DC/DC in Telecoms and Inductrial

TO-263

TO-220



Part Number	Package	Marking
HGB110N10SL	TO-263	GB110N10SL
HGP110N10SL	TO-220	GP110N10SL

Absolute Maximum Ratings at T_j=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C=25℃	73	A
		T_C=100℃	52	
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	190	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.1mH, T_C=25℃	22	mJ
Power Dissipation	P_D	T_C=25℃	125	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	50	℃/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.2	℃/W

Electrical Characteristics at T_j=25℃ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions		Value min	Value typ	Value max	Unit
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA		100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA		1.4	1.9	2.4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=100V, T_j=25℃		-	-	1	μA
		V_{GS}=0V, V_{DS}=100V, T_j=100℃		-	-	100	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V		-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	TO-263	-	8.7	10.7	mΩ
		V_{GS}=4.5V, I_D=20A	TO-263	-	10.7	13.7	mΩ
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	TO-220	-	9	11	mΩ
		V_{GS}=4.5V, I_D=20A	TO-220	-	11	14	mΩ
Transconductance	g_{fs}	V_{DS}=5V, I_D=20A		-	60	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz		-	1.5	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=50V, f=1MHz	-	2275	-	pF
Output Capacitance	C_{oss}		-	162	-	pF
Reverse Transfer Capacitance	C_{rss}		-	7.9	-	pF
Total Gate Charge	Q_g(10V)	V_{DD}=50V, I_D=14A, V_{GS}=10V	-	29	-	nC
Total Gate Charge	Q_g(4.5V)		-	14	-	nC
Gate to Source Charge	Q_{gs}		-	5	-	nC
Gate to Drain (Miller) Charge	Q_{gd}		-	5	-	nC
Turn on Delay Time	$t_{d(on)}$	V_{DD}=50V, I_D=14A, V_{GS}=10V, R_G=10Ω,	-	8	-	ns
Rise time	t_r		-	3	-	ns
Turn off Delay Time	$t_{d(off)}$		-	26	-	ns
Fall Time	t_f		-	4	-	ns

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=50V, I_F=12A, dI_F/dt=500A/μs	-	33	-	ns
Reverse Recovery Charge	Q_{rr}		-	157	-	nC

Fig 1. Typical Output Characteristics

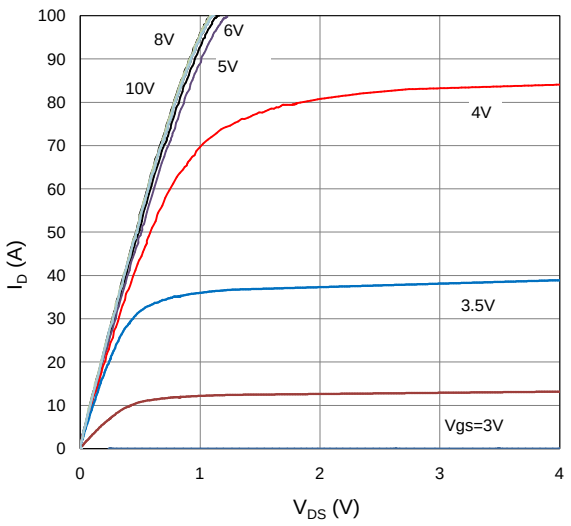


Figure 2. On-Resistance vs. Gate-Source Voltage

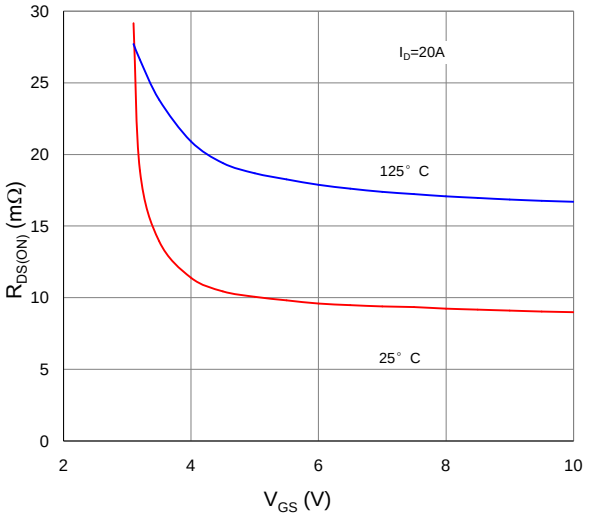


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

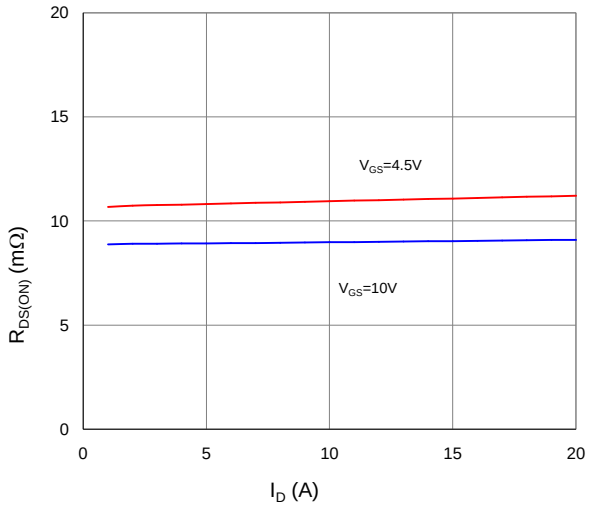


Figure 4. Normalized On-Resistance vs. Junction Temperature

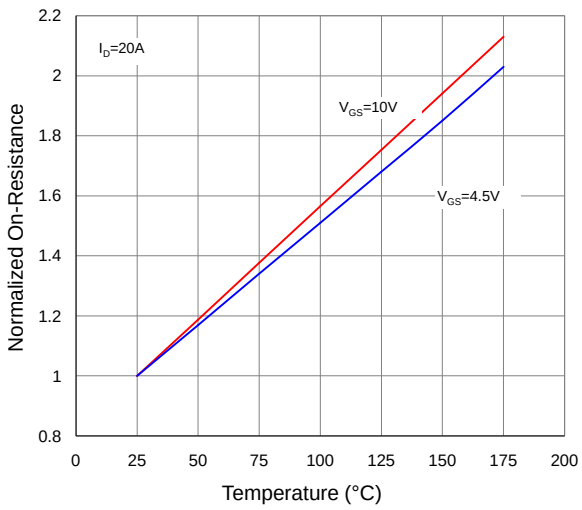


Figure 5. Typical Transfer Characteristics

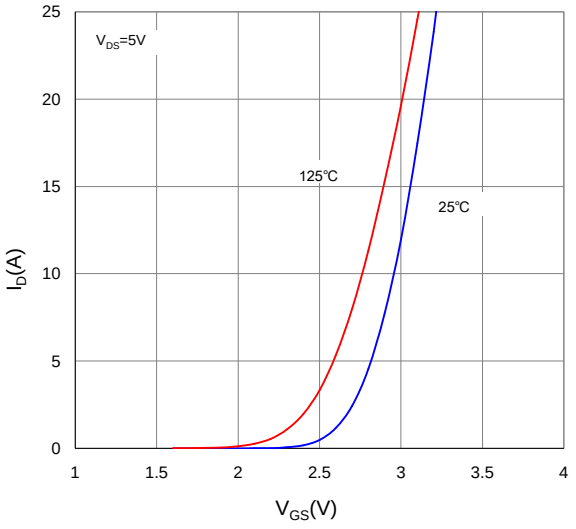


Figure 6. Typical Source-Drain Diode Forward Voltage

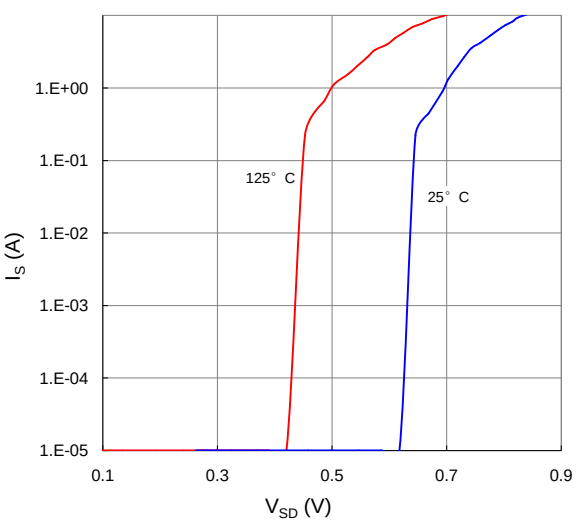


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

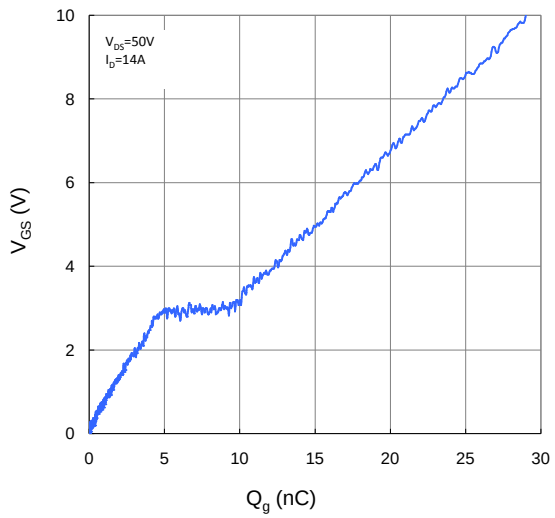


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

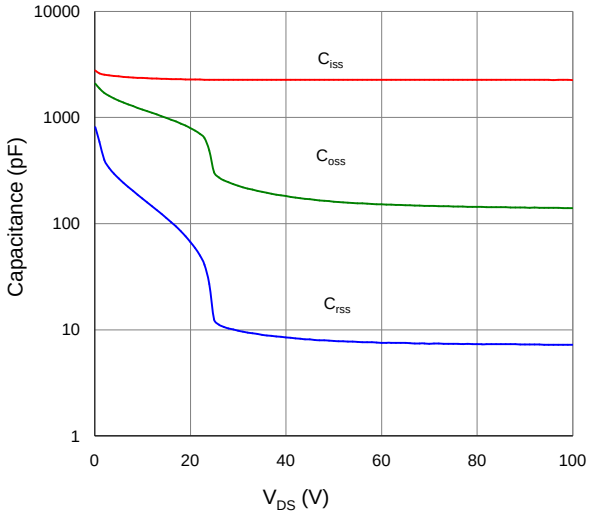


Figure 9. Maximum Safe Operating Area

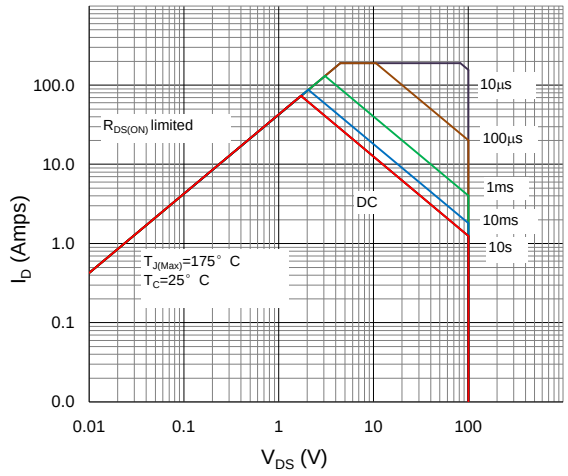


Figure 10. Maximun Drain Current vs. Case Temperature

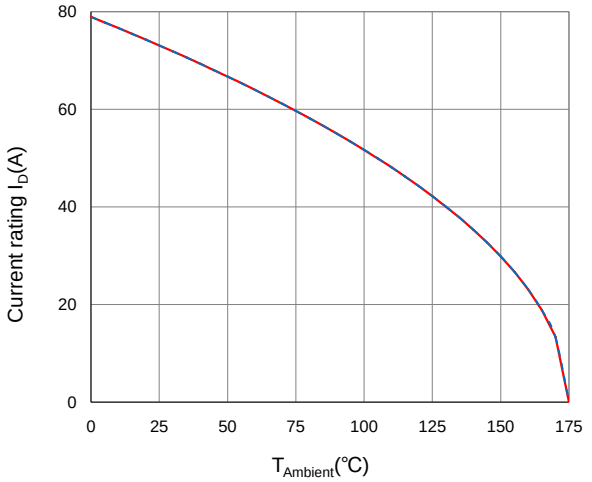
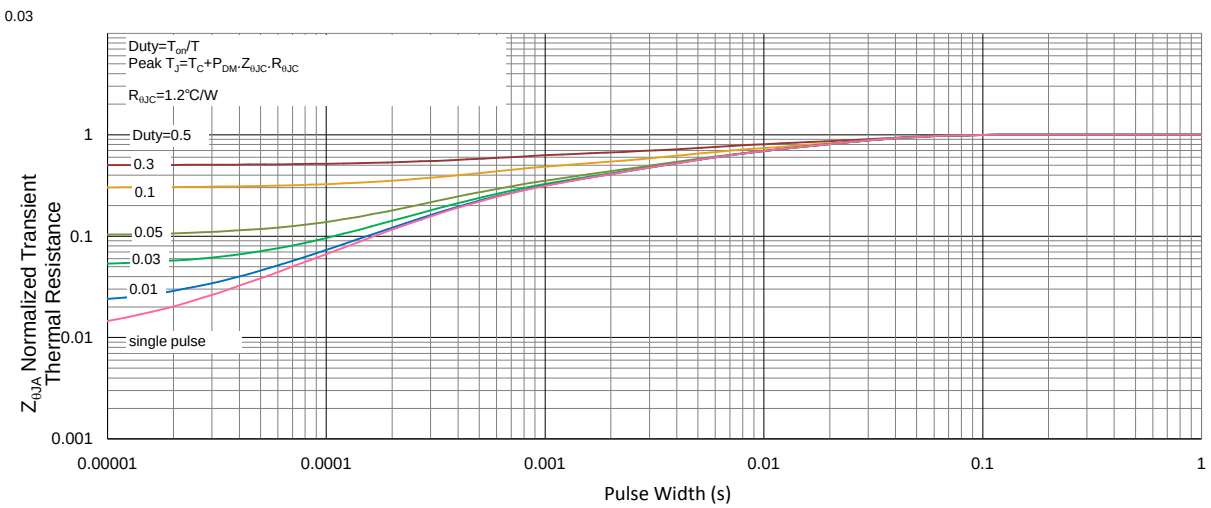
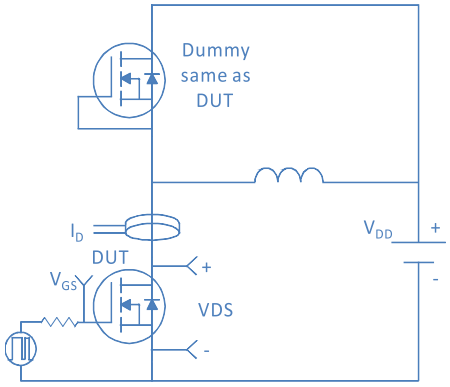
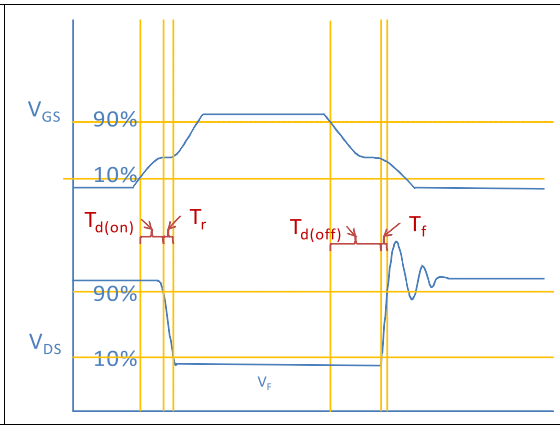


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

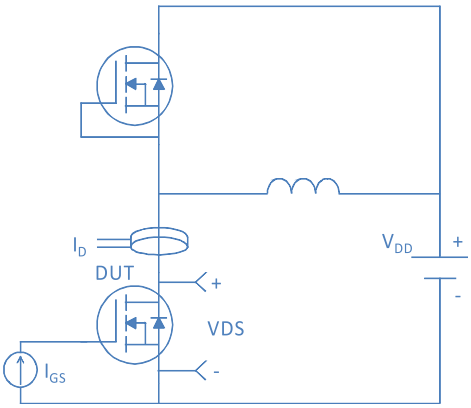


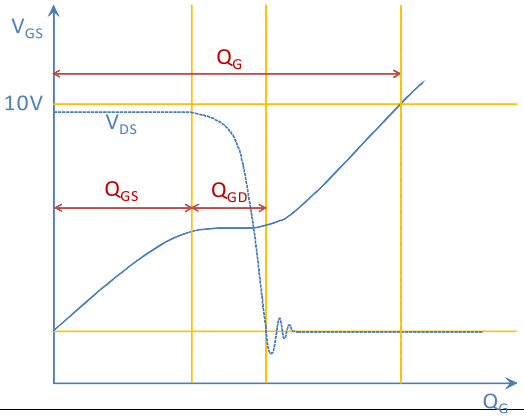
Inductive switching Test



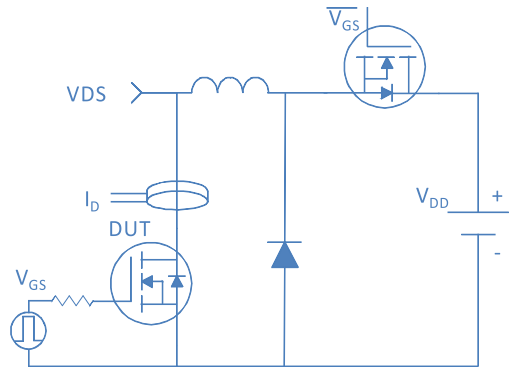


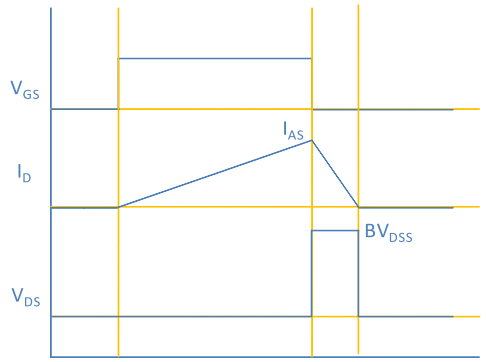
Gate Charge Test



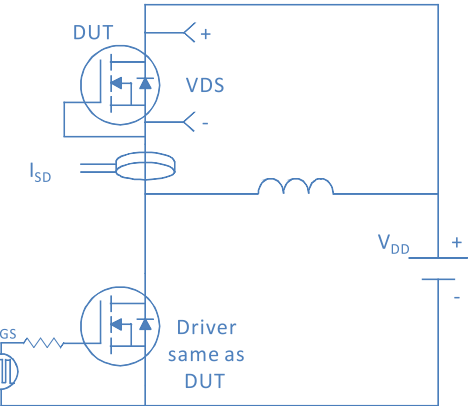


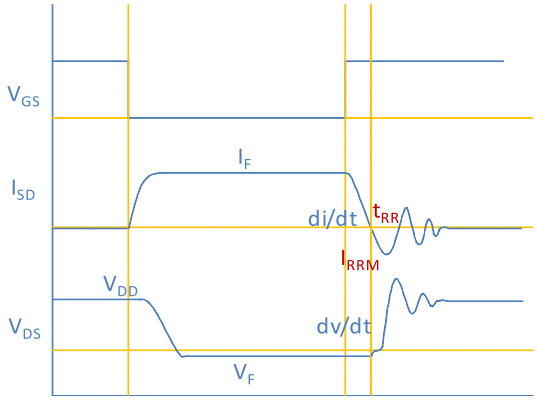
Uclamped Inductive Switching (UIS) Test





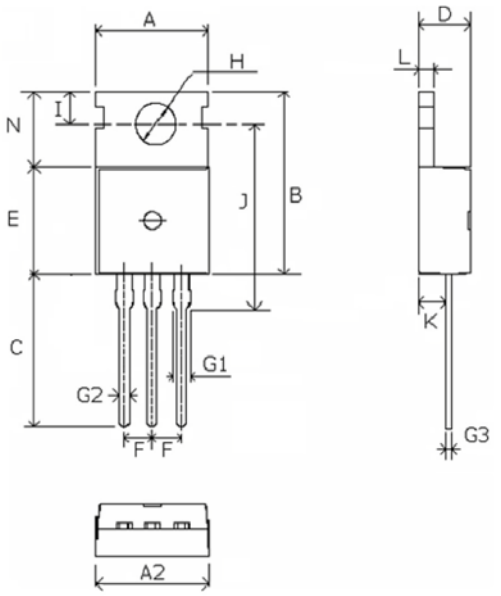
Diode Recovery Test





Package Outline

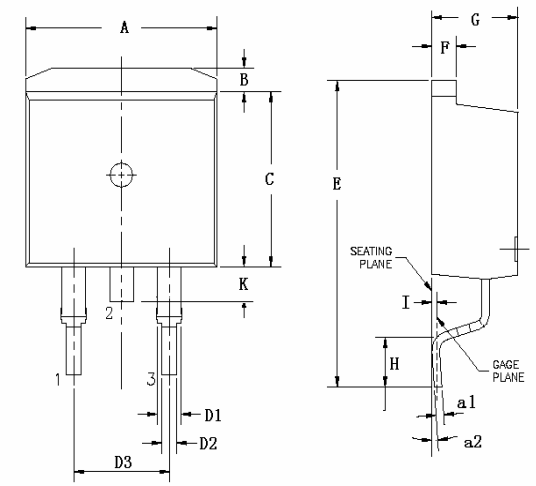
TO-220, 3 leads



Dimentions in mm unless otherwise specified

Symbol	Min	Nom	Max
A	9.66	9.97	10.28
A2	9.80	10.00	10.20
B	15.60	15.70	15.80
C	12.70	13.48	14.27
D	4.30	4.50	4.70
E	9.00	9.20	9.40
F		2.54	
G1	1.32	1.52	1.72
G2	0.70	0.82	0.95
G3	0.45	0.52	0.60
H	3.50	3.60	3.70
I	2.70	2.80	2.90
J	15.70	15.97	16.25
K	2.20	2.40	2.60
L	1.15	1.27	1.40
N	6.40	6.60	6.80

TO-263, 2 leads



Dimentions in mm unless otherwise specified

Symbol	Min	Nom	Max
A	9.66	9.97	10.28
B	1.02	1.17	1.32
C	8.59	9.00	9.40
D1	1.14	1.27	1.40
D2	0.70	0.83	0.95
D3		5.08	
E	15.09	15.24	15.39
F	1.15	1.28	1.40
G	4.30	4.50	4.70
H	2.29	2.54	2.79
I		0.25	
K	1.30	1.45	1.60
a1	0.45	0.55	0.65
a2(degree)	0°		8°